

# SKR 2F50



## Stud Diode

## Fast Recovery Rectifier Diode

### SKR 2F50

### Features

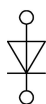
- Small recovered charge
- Soft recovery
- Up to 1000 V reverse voltage
- Hermetic metal case with glass insulator
- Threaded stud ISO M6 or 1/4-28 UNF
- SKR: cathode to stud

### Typical Applications

- Inverse diode for power transistor, GTO thyristor, asymmetric thyristor
- SMPS, inverters, choppers
- For severe ambient conditions

| $V_{RSM}$<br>V | $V_{RRM}$<br>V | $I_{FRMS} = 100$ A (maximum value for continuous operation)<br>$I_{FAV} = 50$ A (sin. 180; 5000 Hz; $T_c = 95$ °C) |  |
|----------------|----------------|--|--|
| 400            | 400            | SKR 2F50/04  |  |
| 400            | 400            | SKR 2F50/04UNF   |  |
| 600            | 600            | SKR 2F50/06  |  |
| 600            | 600            | SKR 2F50/06UNF   |  |
| 800            | 800            | SKR 2F50/08  |  |
| 800            | 800            | SKR 2F50/08UNF   |  |
| 1000           | 1000           | SKR 2F50/10  |  |
| 1000           | 1000           | SKR 2F50/10UNF   |  |

| Symbol        | Conditions                            | Values         | Units            |
|---------------|---------------------------------------|----------------|------------------|
| $I_{FAV}$     | sin. 180; $T_c = 85$ (100) °C         | 57 (46)        | A                |
| $I_{FAV}$     | K3; $T_a = 45$ °C; sin. 180; 5000 Hz  | 17             |                  |
| $I_{FSM}$     | $T_{vj} = 25$ °C; 10 ms               | 800            | A                |
|               | $T_{vj} = 150$ °C; 10 ms              | 670            | A                |
| $i^2t$        | $T_{vj} = 25$ °C; 8,3 ... 10 ms       | 3200           | A <sup>2</sup> s |
|               | $T_{vj} = 150$ °C; 8,3 ... 10 ms      | 2200           | A <sup>2</sup> s |
| $V_F$         | $T_{vj} = 25$ °C; $I_F = 50$ A        | max. 1,8       | V                |
| $V_{(TO)}$    | $T_{vj} = 150$ °C                     | max. 1,2       | V                |
| $r_T$         | $T_{vj} = 150$ °C                     | max. 4         | mΩ               |
| $I_{RD}$      | $T_{vj} = 25$ °C; $V_{RD} = V_{RRM}$  | max. 0,4       | mA               |
| $I_{RD}$      | $T_{vj} = 130$ °C; $V_{RD} = V_{RRM}$ | max. 50        | mA               |
| $Q_{rr}$      | $T_{vj} = 130$ °C; $I_F = 100$ A,     | 3              | μC               |
| $I_{RM}$      | $-di/dt = 30$ A/μs; $V_R = 30$ V      | 10             | A                |
| $t_{rr}$      |                                       | 600            | ns               |
| $E_{rr}$      |                                       | -              | mJ               |
| $R_{th(j-c)}$ |                                       | 0,65           | K/W              |
| $R_{th(c-s)}$ |                                       | 0,25           | K/W              |
| $T_{vj}$      |                                       | - 40 ... + 150 | °C               |
| $T_{stg}$     |                                       | - 55 ... + 150 | °C               |
| $V_{isol}$    |                                       | -              | V~               |
| $M_s$         | to heatsink                           | 2,5            | Nm               |
| $a$           |                                       | 5 * 9,81       | m/s <sup>2</sup> |
| $m$           | approx.                               | 20             | g                |
| Case          |                                       | E 10           |                  |



SKR

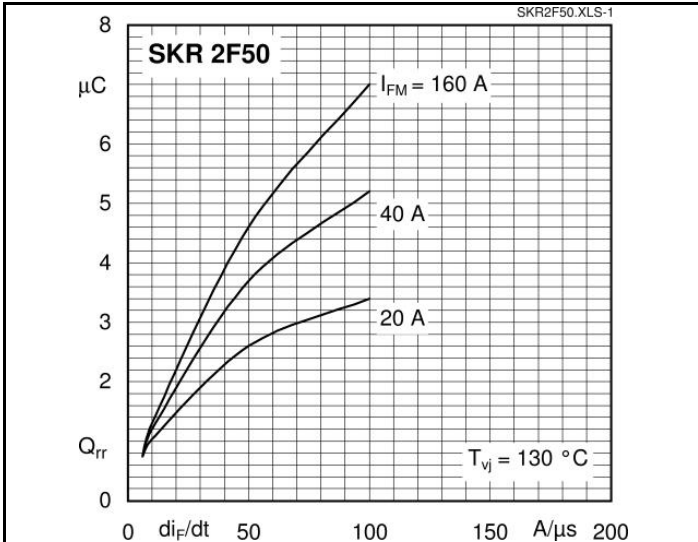


Fig. 1 Typ. recovery charge vs. current decrease

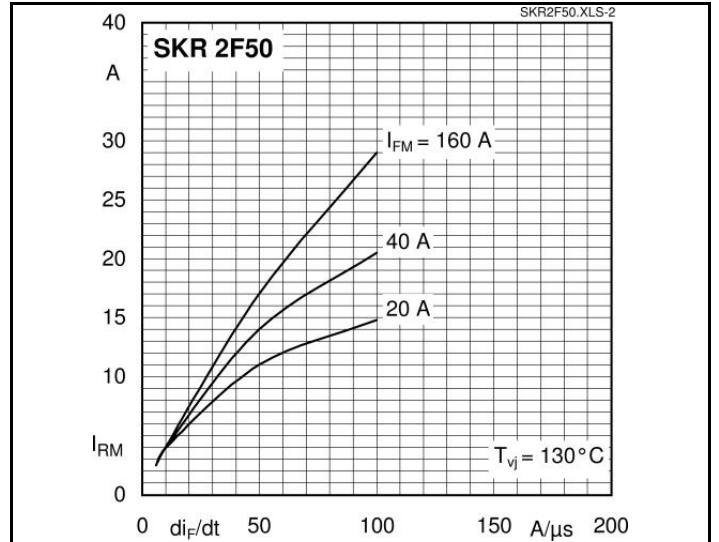


Fig. 2 Peak recovery current vs. current decrease

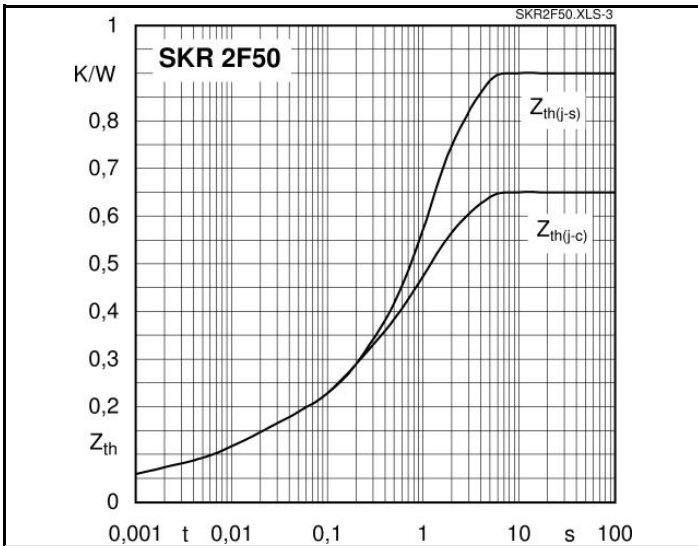


Fig. 3 Transient thermal impedance vs. time

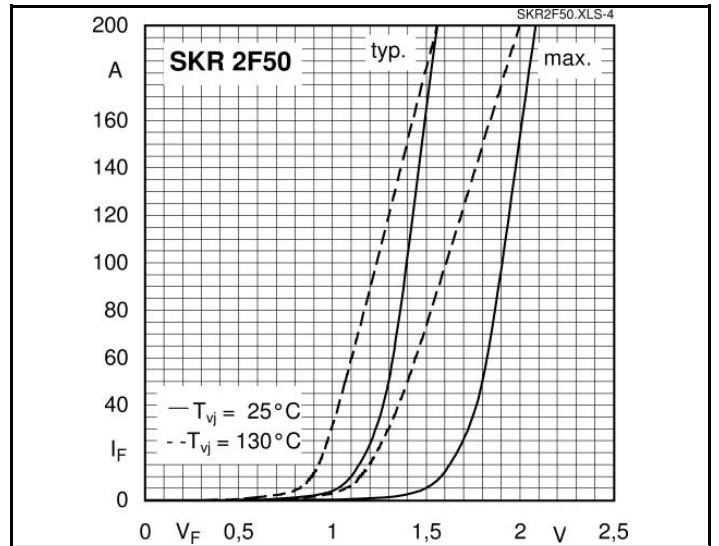


Fig. 4 Forward characteristics

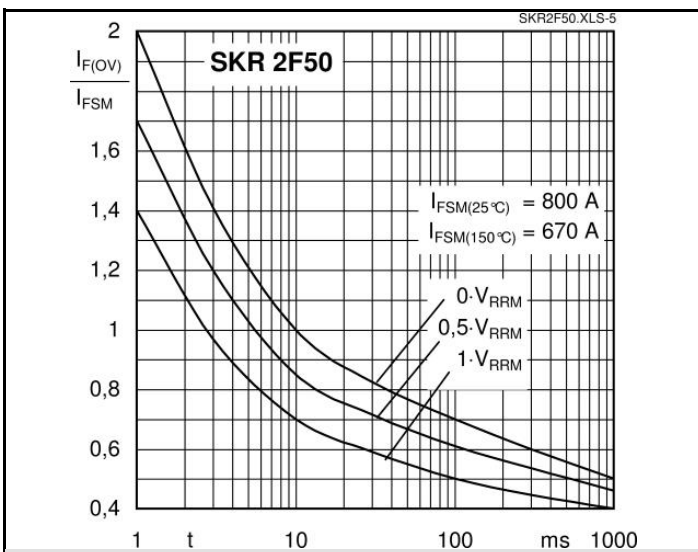
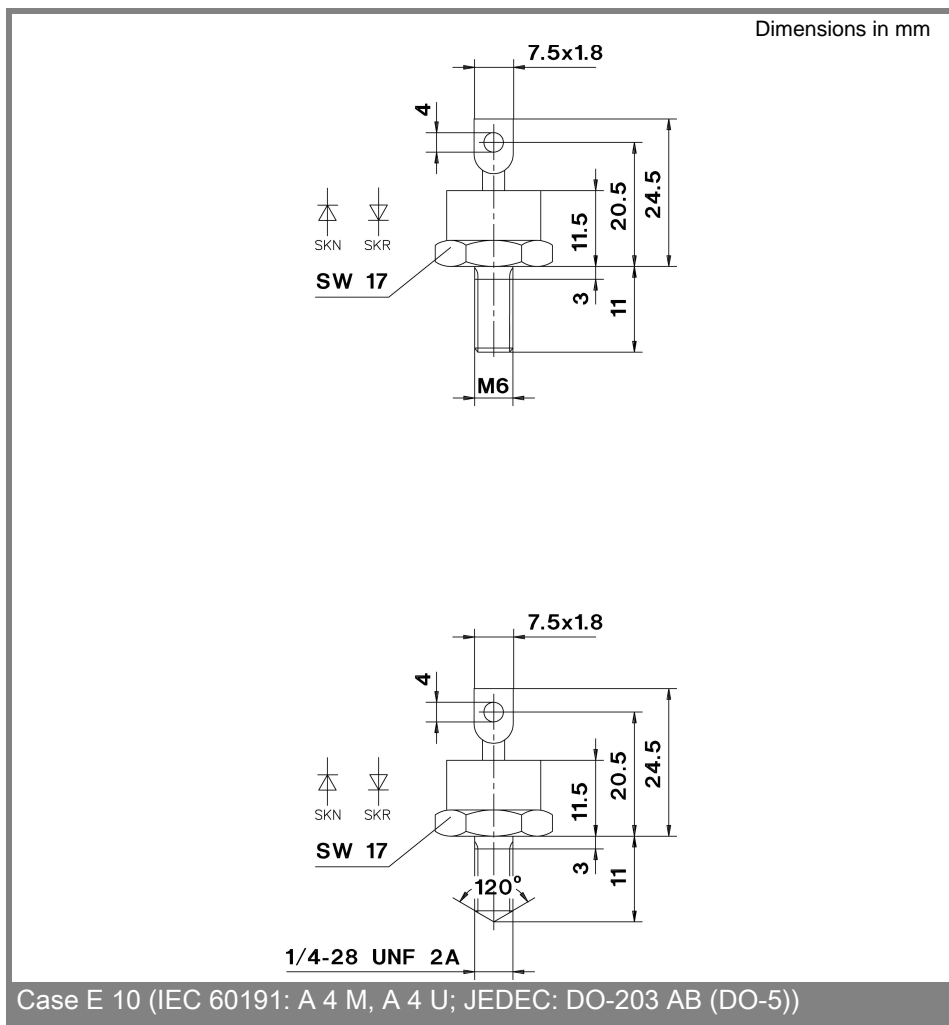


Fig. 5 Surge overload current vs. time



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